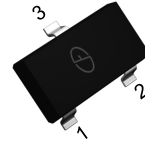


## P-Channel -20V (D-S) Power MOSFET

### Features

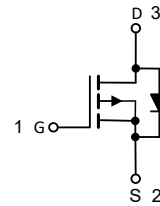
- 100% Avalanche Tested
- Halogen Free, Pb-Free
- RoHS Compliant



SOT-23

### Applications

- Relay driver
- Switching circuits
- High-side load switch
- High-speed line driver



<b>Absolute Maximum Ratings</b> ( $T_A=25^\circ\text{C}$ unless otherwise noted)				
Parameter	Symbol	Value	Unit	
Drain Source Voltage	$V_{DS}$	-20	V	
Gate Source Voltage	$V_{GS}$	$\pm 12$	V	
Drain Current, Continuous $V_{GS}=-10\text{V}$	$I_D$	-3.5	$T_C=25^\circ\text{C}$	A
Drain Current, Pulsed (Note 1)	$I_{DM}$	-14	A	
Power Dissipation	$P_D$	1.25	$T_C=25^\circ\text{C}$	W
Operating Junction/ Storage Temperature Range	$T_J/ T_{STG}$	-55 to +150	$^\circ\text{C}$	

Note 1: Single pulse;  $t_p \leq 1\mu\text{s}$ .

<b>Thermal Characteristics</b>			
Parameter	Symbol	Max	Unit
Thermal Resistance Junction to Ambient (Note 2)	$R_{thJA}$	100	$^\circ\text{C}/\text{W}$

Note 2: Device mounted on 1 square inch FR4 PCB board, with 2oz single-sided copper, in a  $25^\circ\text{C}$  still air environment.

Electrical Characteristics (T <sub>A</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-20	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	--	--	-1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250uA	-0.5	--	-1.0	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	--	--	±100	nA
Drain-Source On-state Resistance (Note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	--	33	40	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-3A	--	45	53	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS(off)</sub> =0V, V <sub>GS(on)</sub> =-4.5V, V <sub>DS</sub> =-8V, I <sub>D</sub> =-3.5A	--	12	--	nC
Gate-Source Charge	Q <sub>gs</sub>		--	1.3	--	
Gate-Drain Charge	Q <sub>gd</sub>		--	2.5	--	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DD</sub> =-10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-0.5A	--	8.5	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	10	--	
Turn-off Delay Time	t <sub>d(off)</sub>		--	39	--	
Turn-off Fall Time	t <sub>f</sub>		--	14	--	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz	--	889	--	pF
Output Capacitance	C <sub>oss</sub>		--	102	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	94	--	

Reverse Diode Characteristics (T <sub>A</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Current, Continuous	I <sub>SD</sub>	T <sub>C</sub> =25°C	--	--	-3.5	A
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	I <sub>F</sub> =-1A, V <sub>GS</sub> =0V	--	-0.8	-1.3	V

Note 3: Pulse test; pulse width ≤ 380μs, duty cycle ≤ 1%.

## Typical Characteristics Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig.1 - Output Characteristics

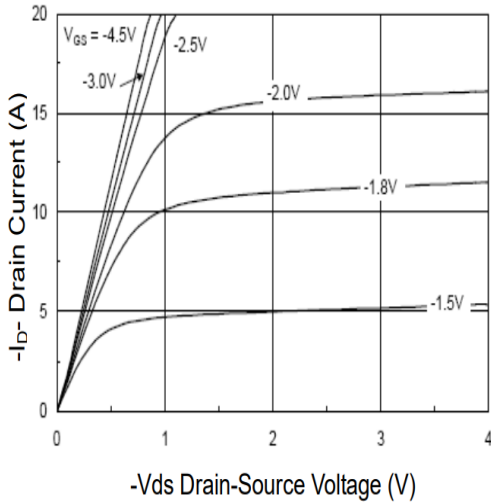


Fig.2 - Transfer Characteristics

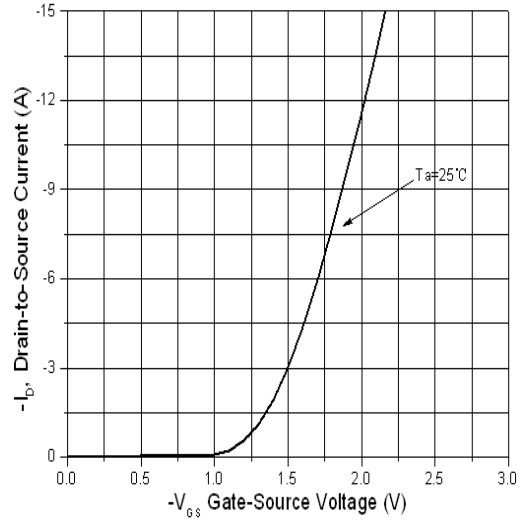


Fig.3 - Normalized On-Resistance

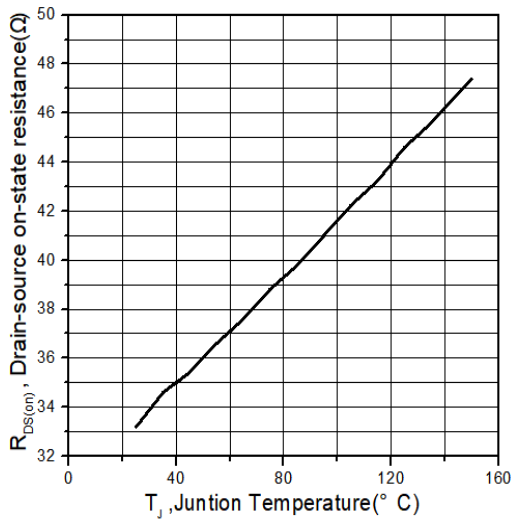


Fig.4 - Normalized Threshold Voltage

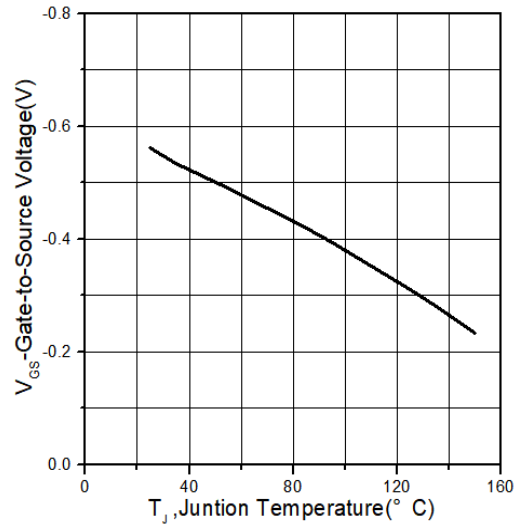


Fig.5 - Capacitance

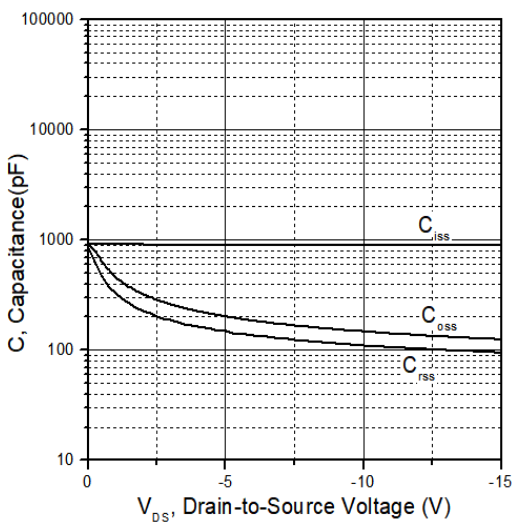
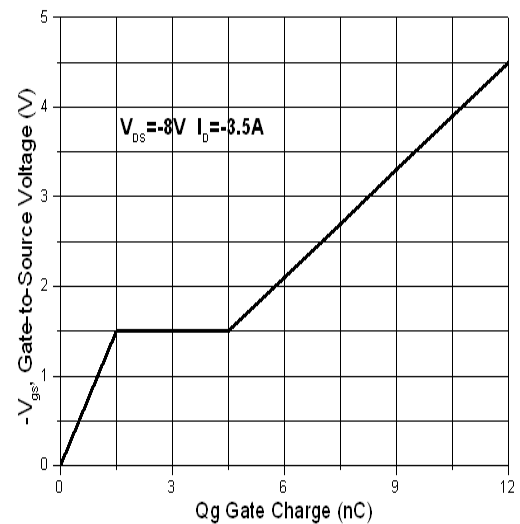


Fig.6 - Gate charge



## Typical Characteristics Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig.7 - Drain-to-Source Breakdown Voltage

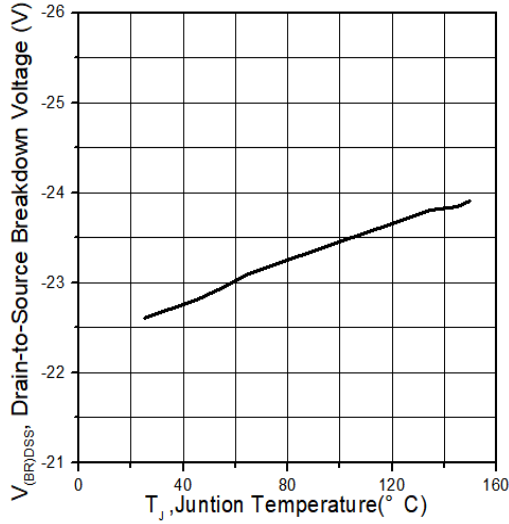


Fig.8 - Drain Current

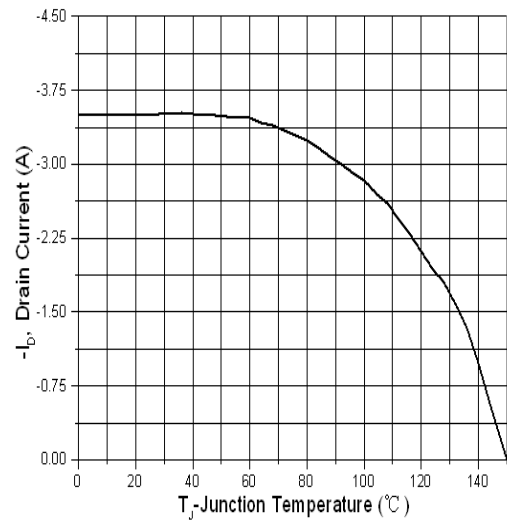
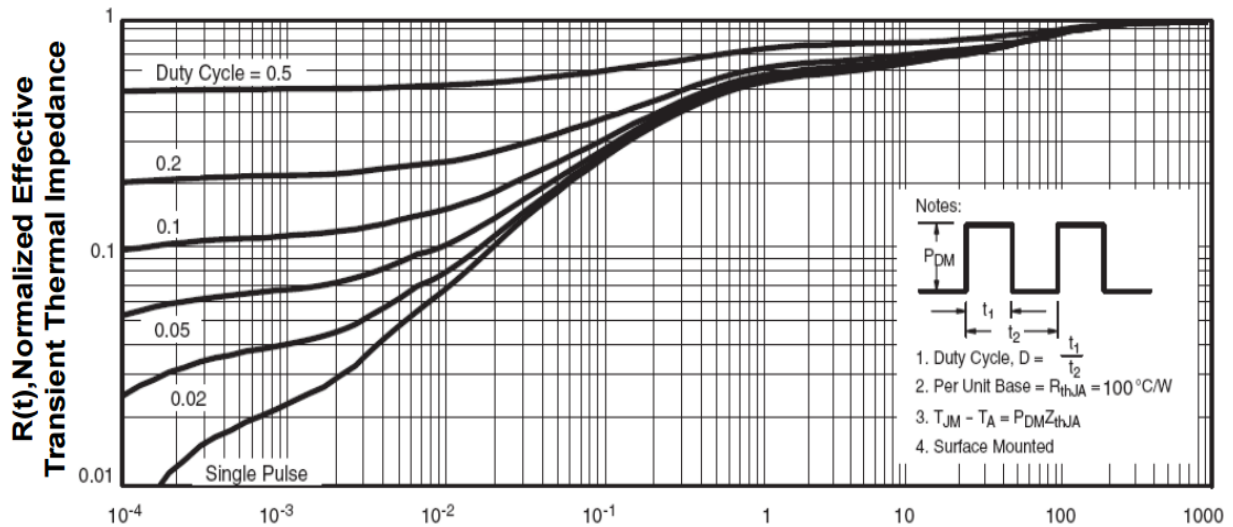
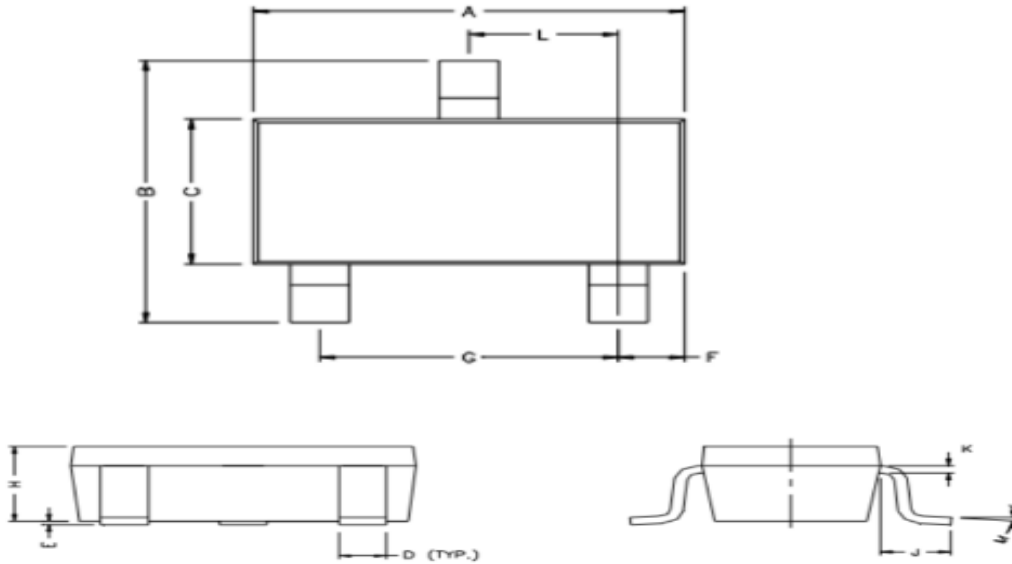


Fig.9 - Normalized Thermal Impedance, Junction-Case



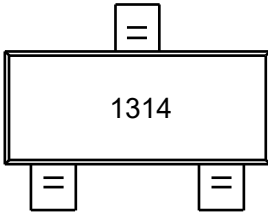
**Package Outline Dimensions** (Unit: millimeters)

**SOT-23**



REF.	Millimeter		REF.	Millimete	
	Min.	Max.		Min.	Max.
A	2.80	3.00	G	1.80	2.00
B	2.30	2.50	H	0.90	1.1
C	1.20	1.40	K	0.10	0.20
D	0.30	0.50	J	0.35	0.70
E	0	0.10	L	0.92	0.98
F	0.45	0.55	M	0°	10°

## Marking Outline



Part Name: GMP1314UP

1. P/N Mark: 1314

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